

UP04878G

Silicon N-channel MOSFET

For switching

■ Features

- Allowing 2.5 V drive
- Incorporating a built-in gate protection-diode
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number

- 2SK3539G × 2

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	50	V
Gate-source voltage (Drain open)	V_{GSO}	± 7	V
Drain current	I_D	100	mA
Peak drain current	I_{DP}	200	mA
Total power dissipation	P_T	125	mW
Channel temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

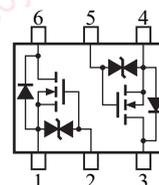
■ Package

- Code
SSMini6-F2
- Pin Name

1: Source (FET1)	4: Source (FET2)
2: Gate (FET1)	5: Gate (FET2)
3: Drain (FET2)	6: Drain (FET1)

■ Marking Symbol:7Y

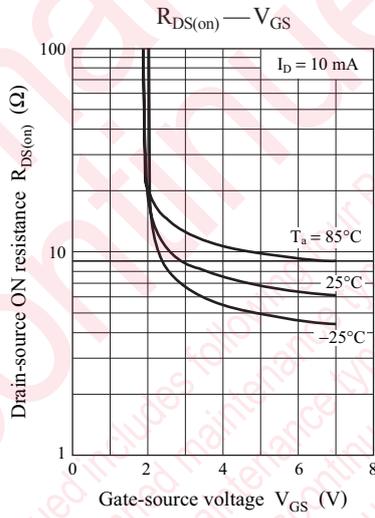
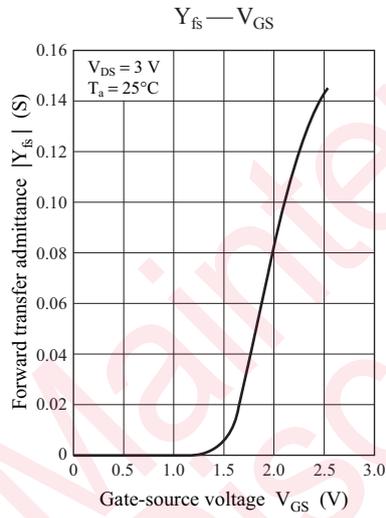
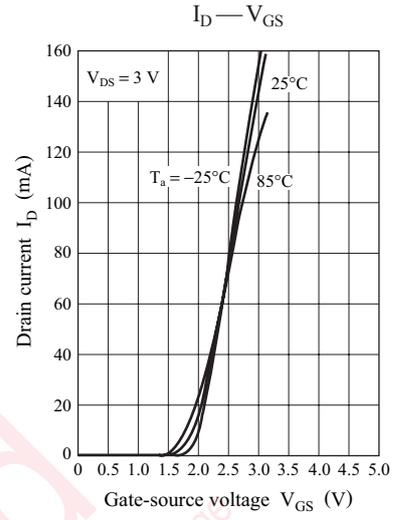
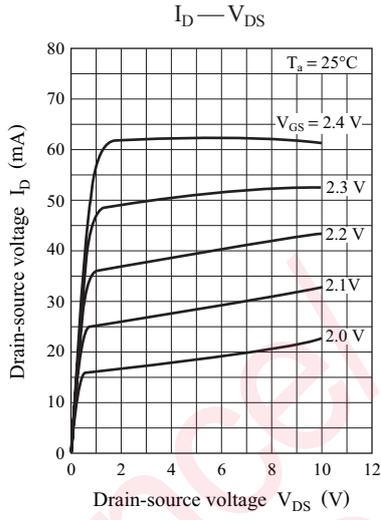
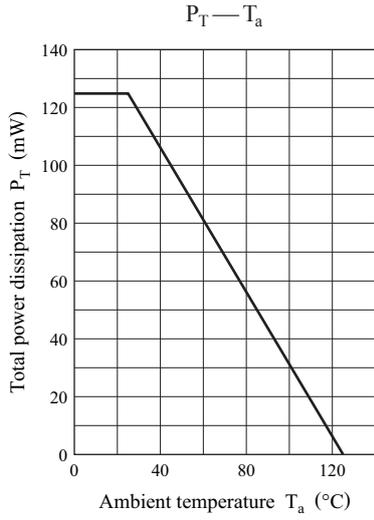
■ Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

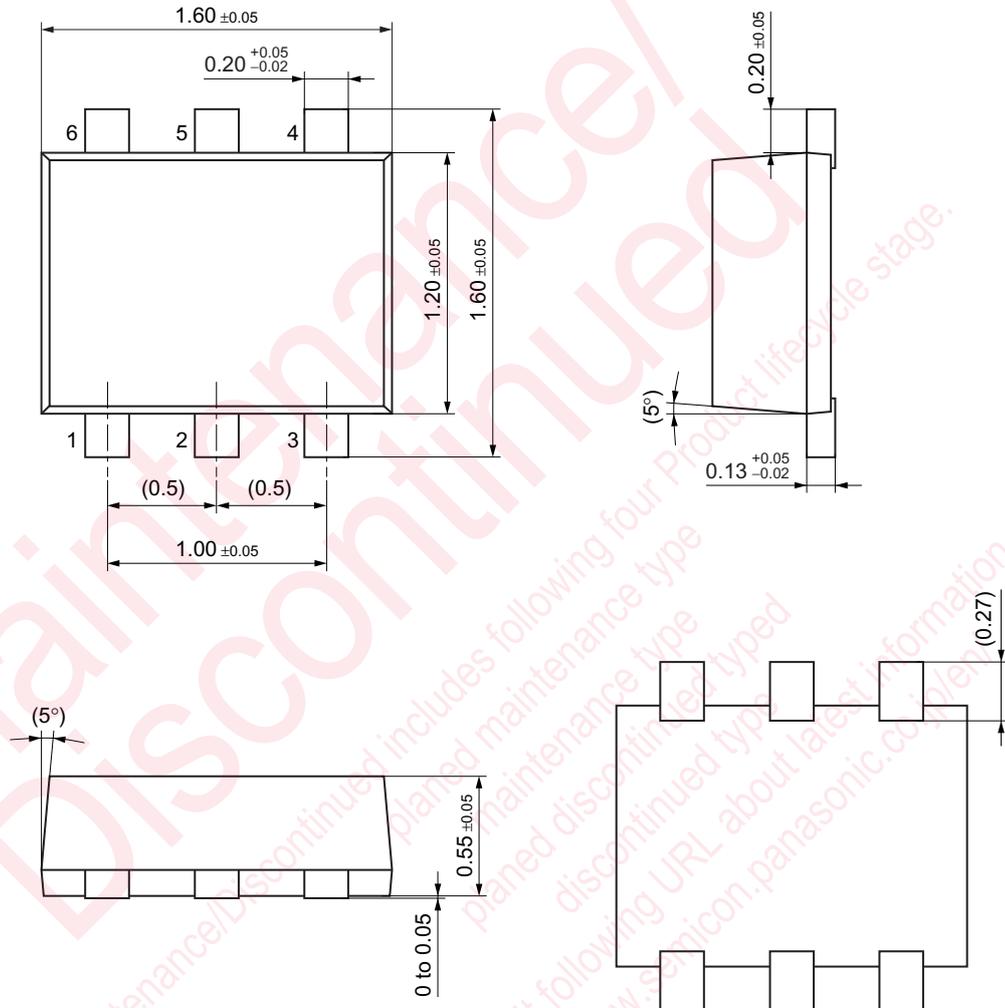
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	V_{DSS}	$I_D = 10 \mu\text{A}$, $V_{GS} = 0$	50			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 50 \text{ V}$, $V_{GS} = 0$			1.0	μA
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 7 \text{ V}$, $V_{DS} = 0$			± 5	μA
Gate threshold voltage	V_{th}	$I_D = 1 \mu\text{A}$, $V_{DS} = 3 \text{ V}$	0.9	1.2	1.5	V
Drain-source ON resistance	$R_{DS(on)}$	$I_D = 10 \text{ mA}$, $V_{GS} = 2.5 \text{ V}$		8	15	Ω
		$I_D = 10 \text{ mA}$, $V_{GS} = 4.0 \text{ V}$		6	12	
Forward transfer conductance	$ Y_{fs} $	$I_D = 10 \text{ mA}$, $V_{GS} = 4.0 \text{ V}$	20	60		mS
Short-circuit input capacitance (Common source)	C_{iss}	$V_{DS} = 3 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		12		pF
Short-circuit output capacitance (Common source)	C_{oss}	$V_{DS} = 3 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		7		pF
Reverse transfer capacitance (Common source)	C_{rss}	$V_{DS} = 3 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		3		pF
Turn-on time	t_{on}	$V_{DD} = 3 \text{ V}$, $V_{GS} = 0 \text{ V}$ to 3 V , $R_L = 470 \Omega$		200		ns
Turn-off time	t_{off}	$V_{DD} = 3 \text{ V}$, $V_{GS} = 3 \text{ V}$ to 0 V , $R_L = 470 \Omega$		200		ns

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



SSMini6-F2

Unit: mm



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